UNIKC Semiconductor

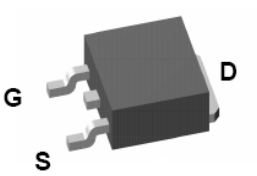
RoHS Compliant

P6015CDG

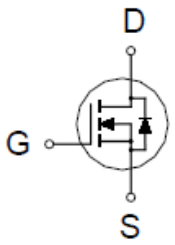
N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
150V	60mΩ @V_{GS} = 10V	20A



TO-252



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	±12	V
Continuous Drain Current	T_C = 25 °C	I_D	20	A
	T_C = 100 °C		15	
Pulsed Drain Current[1]		I_{DM}	60	
Avalanche Current		I_{AS}	20	
Avalanche Energy	L = 0.47mH	E_{AS}	94	mJ
Repetitive Avalanche Energy[2]	L = 0.47mH	E_{AR}	35	
Power Dissipation	T_C = 25 °C	P_D	48	W
	T_C = 100 °C		20	
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C
Lead Temperature ($^1/_{16}$" from case for 10 sec.)		T_L	275	

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		2.6	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	

[1]Pulse width limited by maximum junction temperature.

[2]Duty cycle ≤ 1%.

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PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	150			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	0.45	0.75	1.20	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±12V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 120V, V_{GS} = 0V			1	μA
		V_{DS} = 100V, V_{GS} = 0V , T_J = 125 °C			10	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 5V, V_{GS} = 5V	60			A
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 3V, I_D = 3A		62	80	mΩ
		V_{GS} = 5V, I_D = 10A		56	70	
		V_{GS} = 10V, I_D = 15A		50	60	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 10A		26		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		7660		pF
Output Capacitance	C_{oss}			725		
Reverse Transfer Capacitance	C_{rss}			420		
Total Gate Charge[2]	Q_g	V_{DS} = 0.5$V_{(BR)DSS}$, V_{GS} = 4.5V, I_D = 10A		107	140	nC
Gate-Source Charge[2]	Q_{gs}			18		
Gate-Drain Charge[2]	Q_{gd}			60		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DS} = 75V, I_D ≅ 10A, V_{GS} = 10V, R_{GS} = 16Ω		18		nS
Rise Time[2]	t_r			115		
Turn-Off Delay Time[2]	$t_{d(off)}$			338		
Fall Time[2]	t_f			384		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I_S				20	A
Pulsed Current[3]	I_{SM}				60	
Forward Voltage[1]	V_{SD}	I_F = I_S, V_{GS} = 0V			1.3	V
Reverse Recovery Time	t_{rr}	I_F = I_S, dI_F/dt = 100A / μS		57		nS
Peak Reverse Recovery Current	$I_{RM(REC)}$			60		A
Reverse Recovery Charge	Q_{rr}			0.13		μC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

[3]Pulse width limited by maximum junction temperature.

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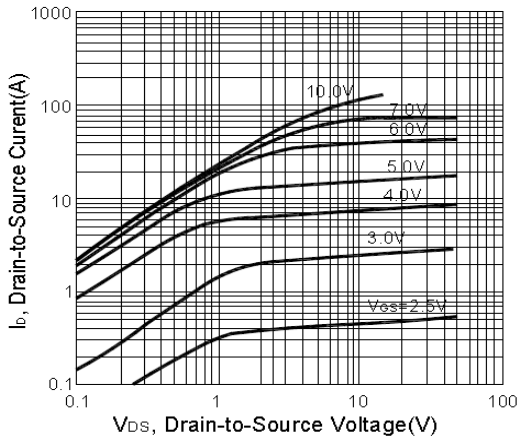
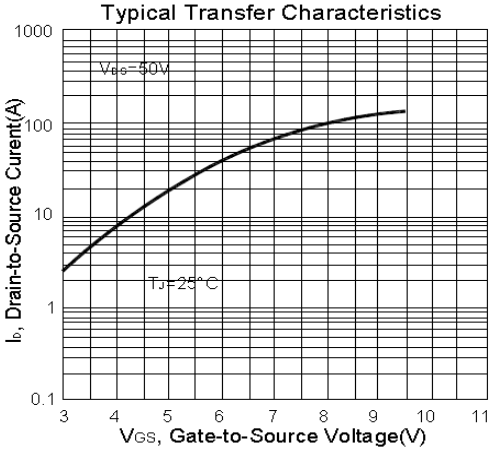
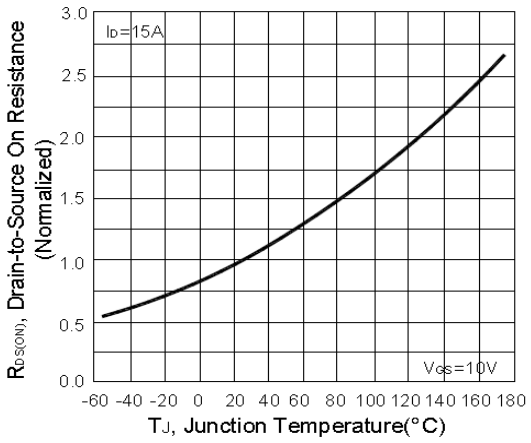
Typical Output Characteristics



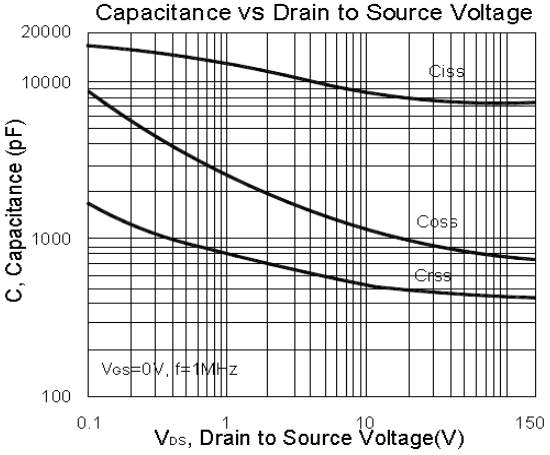
Typical Transfer Characteristics



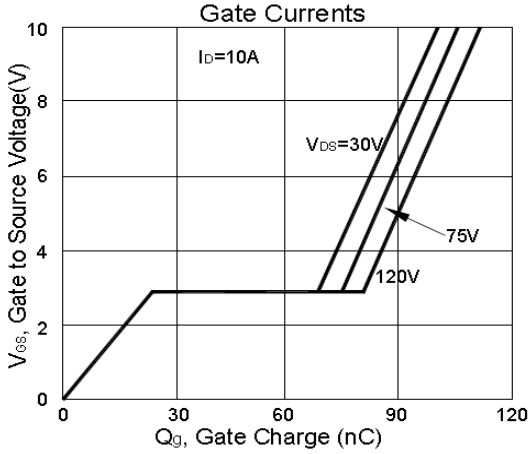
Normalized On- Resistance Vs. Temperature



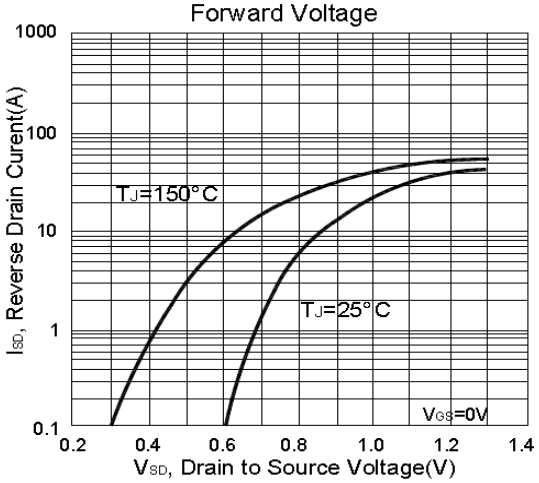
Capacitance vs Drain to Source Voltage



Gate Charge Waveforms for Constant Gate Currents



Typical Source-Drain Diode Forward Voltage



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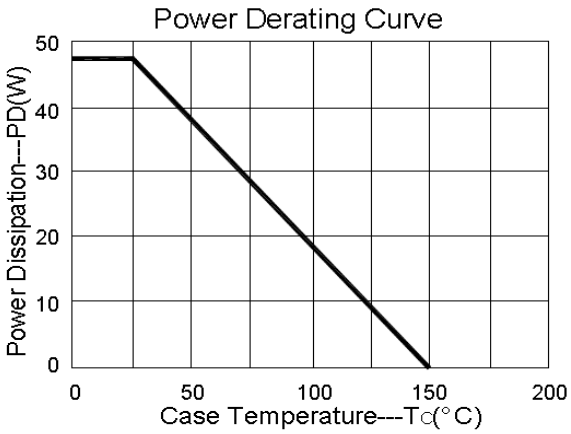

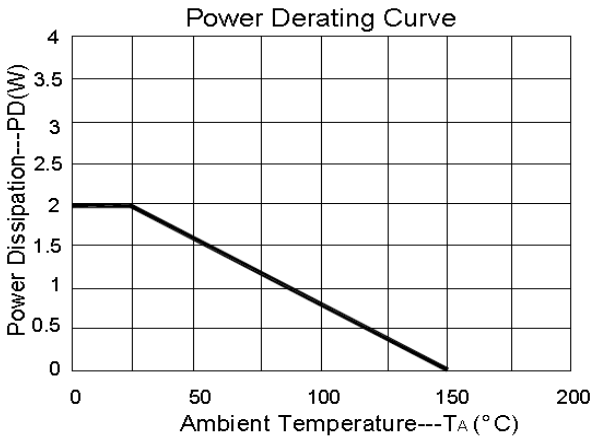

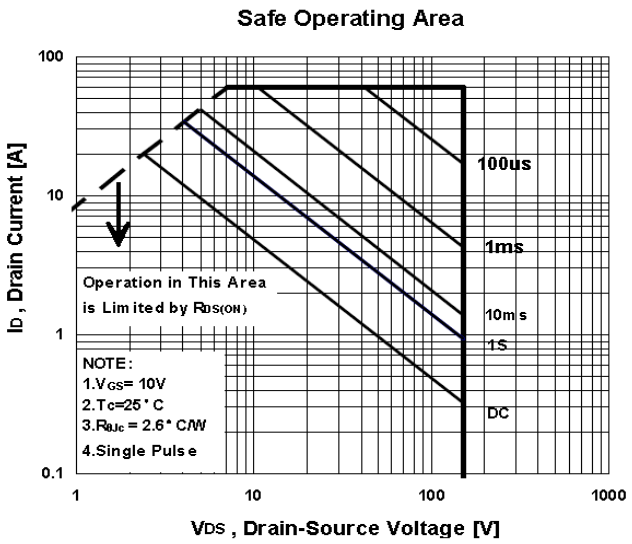

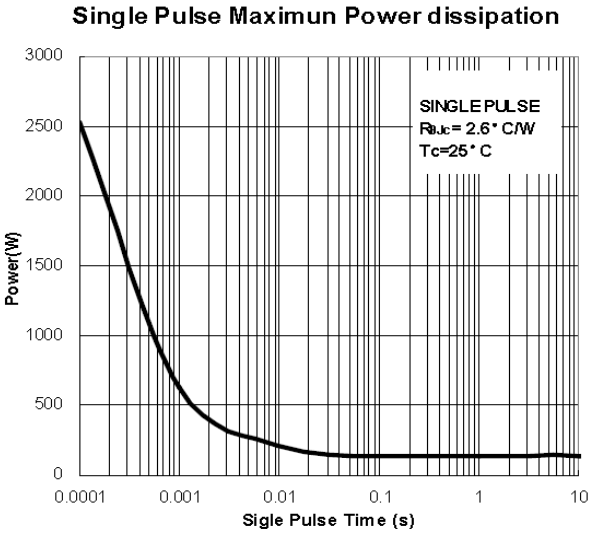

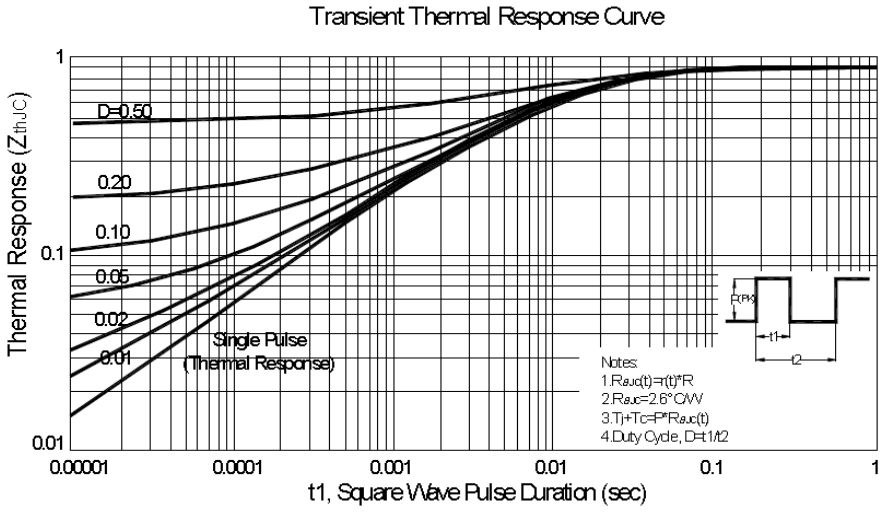

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Package Dimension

TO-252 (DPAK) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	8.9	10	10.41	J	4.8		5.64
B	2.1	2.2	2.5	K	0.15		1.49
C	0.4	0.5	0.61	L	0.4	0.76	0.91
D	0.82	1.2	1.5	M	4.2	4.58	5
E	0.35	0.5	0.65	S	4.57	5.1	5.52
F	0		0.2	T	3.81	4.75	5.24
G	5.3	6.1	6.3	U	1.4		1.78
H	0.5		1.7	V	0.55	1.25	1.7
I	6.3	6.5	6.8